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Attorney Docket No. COVA0003 DIV  
Client/Matter No. 90337.0006.001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Klaus Dimmler, Alfred P. Gnadinger

Serial No. -----

Filed: Herewith

For: FERROELECTRIC TRANSISTOR WITH  
ENHANCED DATA RETENTION

Customer No. 25235

Group Art Unit:

Examiner:

Confirmation No.:

INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. 1.97

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

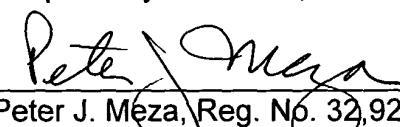
Pursuant to 37 C.F.R. § 1.97, the Examiner may wish to consider the references listed on the attached Form PTO/SB/08A. In submitting these references, no representation is made or implied that the references are or are not material to the examination of this application.

This Information Disclosure Statement is filed before mailing of a first Office Action in the above case. Accordingly, no fee is believed due. However, any fee associated herewith may be charged to Deposit Account No. 50-1123.

Respectfully submitted,

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7/15/03

  
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PTO/SB/08A (10/01) (Substitute for form 1449A/PTO)		ATTY. DOCKET NO. COVA0003 DIV Client/Matter No. 90337.0006.001	APPLICATION NO. _____
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		WO98/98/13300	02/04/1998	Kawamura			

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